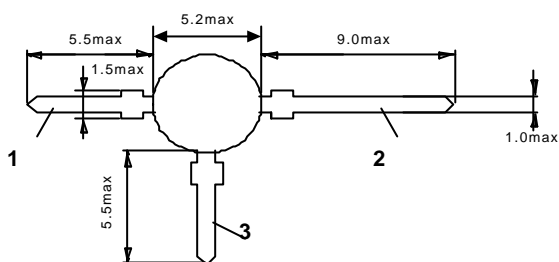


## BFR96

N-P-N bipolar silicon RF transistor  
in plastic package SOT-37



### Pinouts:

1- Base, 2- Collector, 3-Emitter

### Ratings

Symbol	Parameter, unit	Limits
$V_{CBO}$	Collector- base voltage, V	20
$V_{CEO}$	Collector- emitter voltage, V	15
$V_{EBO}$	Emitter- base voltage, V	3
$I_C$	Collector current, mA	75
$P_{tot}$	Power dissipation, mW	700

### Characteristics ( $T_A = 25^\circ\text{C}$ )

Symbol	Parameter, unit, test conditions	Limits	
		min	max
$f_T$	Transition frequency, GHz, $I_E=50\text{mA}$ , $V_{CB}=10\text{V}$	3.2	
$h_{FE}$	DC current gain, $I_E=50\text{mA}$ , $V_{CB}=10\text{V}$	50	
$I_{CBO}$	Collector cut-off current, nA, $I_E=0\text{mA}$ , $V_{CB}=10\text{V}$		100
$G_{PS}$	Power gain, dB, $I_E=50\text{mA}$ , $V_{CE}=10\text{V}$ , $f=500\text{MHz}$	13.0	
$F$	Noise figure, dB $I_E=50\text{mA}$ , $V_{CE}=10\text{V}$ , $f=500\text{MHz}$		4.0
$C_C$	Collector capacitance, pF, $V_{CB}=10\text{V}$ , $f=1\text{MHz}$		2.0